

# NSTB60BDW1

## PNP General Purpose and NPN Bias Resistor Transistor Combination

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- Available in 8 mm, 7 inch/3000 Unit Tape and Reel
- ESD Rating – Human Body Model: Class 1B  
– Machine Model: Class B
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### MAXIMUM RATINGS

( $T_A = 25^\circ\text{C}$  unless otherwise noted, common for  $Q_1$  and  $Q_2$ )

| Rating                         | Symbol    | $Q_1$ | $Q_2$ | Unit |
|--------------------------------|-----------|-------|-------|------|
| Collector-Emitter Voltage      | $V_{CEO}$ | -50   | 50    | Vdc  |
| Collector-Base Voltage         | $V_{CBO}$ | -50   | 50    | Vdc  |
| Emitter-Base Voltage           | $V_{EBO}$ | -6.0  | 5.0   | Vdc  |
| Collector Current – Continuous | $I_C$     | -150  | 150   | mAdc |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

### THERMAL CHARACTERISTICS

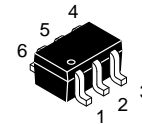
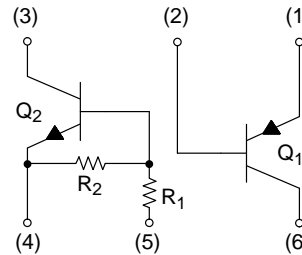
| Characteristic (One Junction Heated)  | Symbol          | Max  | Unit                       |
|---|-----------------|--|----------------------------|
| Total Device Dissipation<br>$T_A = 25^\circ\text{C}$<br>Derate above $25^\circ\text{C}$ | $P_D$           | 187 (Note 1)<br>256 (Note 2)<br>1.5 (Note 1)<br>2.0 (Note 2) | mW<br>mW/ $^\circ\text{C}$ |
| Thermal Resistance –<br>Junction-to-Ambient   | $R_{\theta JA}$ | 670 (Note 1)<br>490 (Note 2)                                 | $^\circ\text{C}/\text{W}$  |
| Characteristic (Both Junctions Heated)  | Symbol          | Max  | Unit                       |
| Total Device Dissipation<br>$T_A = 25^\circ\text{C}$<br>Derate above $25^\circ\text{C}$ | $P_D$           | 250 (Note 1)<br>385 (Note 2)<br>2.0 (Note 1)<br>3.0 (Note 2) | mW<br>mW/ $^\circ\text{C}$ |
| Thermal Resistance –<br>Junction-to-Ambient   | $R_{\theta JA}$ | 493 (Note 1)<br>325 (Note 2)                                 | $^\circ\text{C}/\text{W}$  |
| Thermal Resistance –<br>Junction-to-Lead  | $R_{\theta JL}$ | 188 (Note 1)<br>208 (Note 2)                                 | $^\circ\text{C}/\text{W}$  |
| Junction and Storage Temperature  | $T_J, T_{stg}$  | -55 to +150  | $^\circ\text{C}$           |

1. FR-4 @ Minimum Pad
2. FR-4 @ 1.0 x 1.0 inch Pad



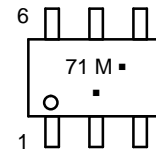
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SOT-363  
CASE 419B  
STYLE 1

### MARKING DIAGRAM



71 = Device Code  
M = Date Code\*  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation may vary depending upon manufacturing location.

### ORDERING INFORMATION

| Device         | Package              | Shipping†          |
|----------------|----------------------|--------------------|
| NSTB60BDW1T1G  | SOT-363<br>(Pb-Free) | 3000 / Tape & Reel |
| NSVTB60BDW1T1G | SOT-363<br>(Pb-Free) | 3000 / Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

# NSTB60BDW1

## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

| Characteristic   | Symbol        | Min  | Typ | Max  | Unit          |
|--|---------------|------|-----|------|---------------|
| <b>Q<sub>1</sub></b>   |               |      |     |      |               |
| Collector-Base Breakdown Voltage ( $I_C = -50 \mu\text{Adc}$ , $I_E = 0$ )                                 | $V_{(BR)CBO}$ | -50  | -   | -    | Vdc           |
| Collector-Emitter Breakdown Voltage<br>( $I_C = -1.0 \text{ mAdc}$ , $I_B = 0$ )                           | $V_{(BR)CEO}$ | -50  | -   | -    | Vdc           |
| Emitter-Base Breakdown Voltage ( $I_E = -50 \mu\text{Adc}$ , $I_C = 0$ )                                   | $V_{(BR)EBO}$ | -6.0 | -   | -    | Vdc           |
| Collector-Base Cutoff Current ( $V_{CB} = -50 \text{ Vdc}$ , $I_E = 0$ )                                   | $I_{CBO}$     | -    | -   | -0.1 | $\mu\text{A}$ |
| Emitter-Base Cutoff Current ( $V_{EB} = -6.0 \text{ Vdc}$ , $I_B = 0$ )                                    | $I_{EBO}$     | -    | -   | -0.1 | $\mu\text{A}$ |
| Collector-Emitter Saturation Voltage<br>( $I_C = -50 \text{ mAdc}$ , $I_B = -5.0 \text{ mAdc}$ ) (Note 3)  | $V_{CE(sat)}$ | -    | -   | -0.5 | Vdc           |
| DC Current Gain ( $V_{CE} = -10 \text{ V}$ , $I_C = -5.0 \text{ mA}$ ) (Note 3)                            | $h_{FE}$      | 120  | -   | 560  | -             |
| Transition Frequency<br>( $V_{CE} = -12 \text{ Vdc}$ , $I_C = -2.0 \text{ mAdc}$ , $f = 100 \text{ MHz}$ ) | $f_T$         | -    | 140 | -    | MHz           |
| Output Capacitance ( $V_{CB} = -12 \text{ Vdc}$ , $I_E = 0 \text{ Adc}$ , $f = 1.0 \text{ MHz}$ )          | $C_{OB}$      | -    | 3.5 | -    | pF            |

## Q<sub>2</sub>

|   |               |      |      |      |                  |
|---|---------------|------|------|------|------------------|
| Collector-Base Breakdown Voltage ( $I_C = 50 \mu\text{A}$ , $I_E = 0$ )   | $V_{(BR)CBO}$ | 50   | -    | -    | Vdc              |
| Collector-Emitter Breakdown Voltage<br>( $I_C = 1.0 \text{ mA}$ , $I_B = 0$ ) (Note 3)                            | $V_{(BR)CEO}$ | 50   | -    | -    | Vdc              |
| Collector-Base Cutoff Current ( $V_{CB} = 50 \text{ V}$ , $I_E = 0$ )   | $I_{CBO}$     | -    | -    | 100  | nAdc             |
| Collector-Emitter Cutoff Current ( $V_{CE} = 50 \text{ V}$ , $I_B = 0$ )  | $I_{CEO}$     | -    | -    | 500  | nAdc             |
| Emitter-Base Cutoff Current ( $V_{EB} = 6.0 \text{ V}$ , $I_C = 0$ )  | $I_{EBO}$     | -    | -    | 0.13 | mAdc             |
| Collector-Emitter Saturation Voltage<br>( $I_C = 10 \text{ mA}$ , $I_B = 5.0 \text{ mA}$ ) (Note 3)               | $V_{CE(sat)}$ | -    | -    | 0.25 | Vdc              |
| DC Current Gain ( $V_{CE} = 10 \text{ V}$ , $I_C = 5.0 \text{ mA}$ ) (Note 3)                                     | $h_{FE}$      | 80   | -    | -    |                  |
| Output Voltage (on) ( $V_{CC} = 5.0 \text{ V}$ , $V_B = 4.0 \text{ V}$ , $R_L = 1.0 \text{ k}\Omega$ ) (Note 3)   | $V_{OL}$      | -    | -    | 0.2  | Vdc              |
| Output Voltage (off) ( $V_{CC} = 5.0 \text{ V}$ , $V_B = 0.25 \text{ V}$ , $R_L = 1.0 \text{ k}\Omega$ ) (Note 3) | $V_{OH}$      | 4.9  | -    | -    | Vdc              |
| Input Resistor (Note 3)   | R1            | 15.4 | 22   | 28.6 | $\text{k}\Omega$ |
| Resistor Ratio (Note 3)   | R2/R1         | 1.70 | 2.13 | 2.55 |                  |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: Pulse Width < 300  $\mu\text{s}$ , Duty Cycle < 2.0%

TYPICAL ELECTRICAL CHARACTERISTICS – PNP Transistor

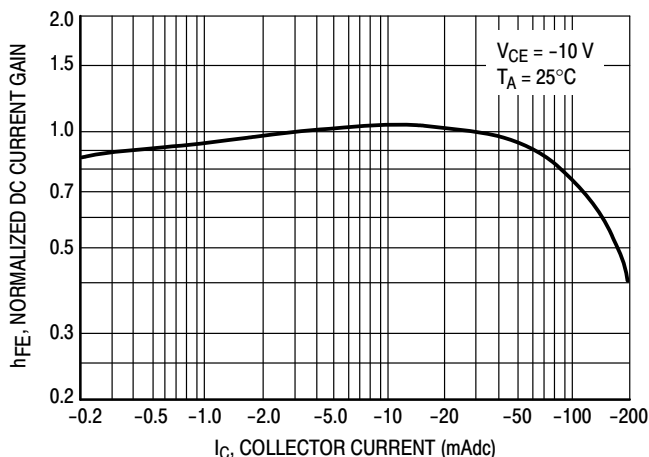


Figure 1. Normalized DC Current Gain

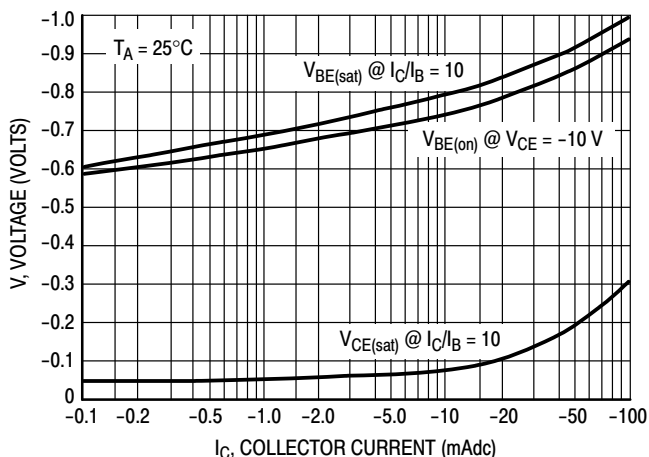


Figure 2. "Saturation" and "On" Voltages

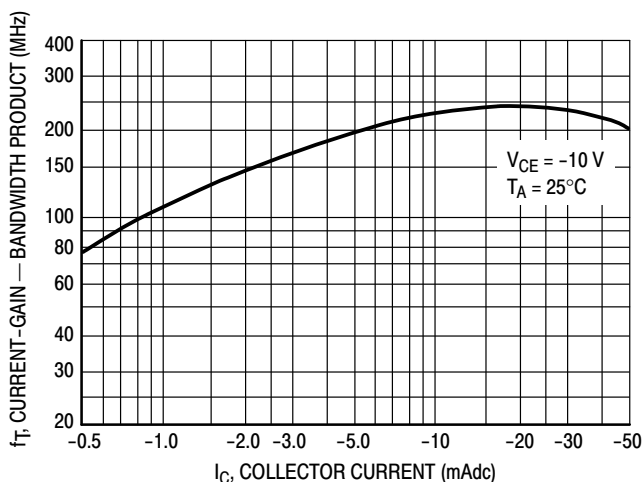


Figure 3. Current-Gain - Bandwidth Product

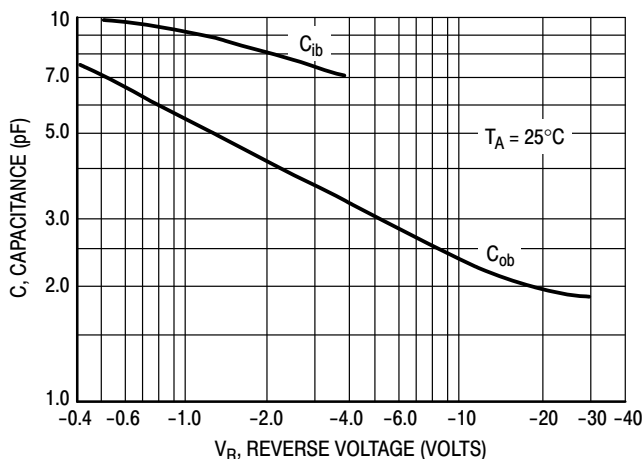


Figure 4. Capacitances

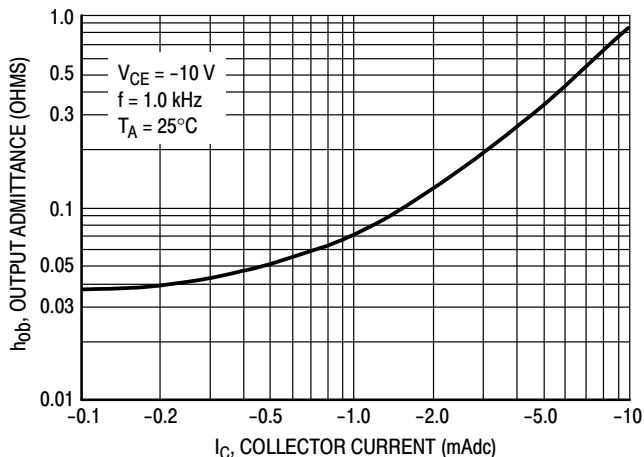


Figure 5. Output Admittance

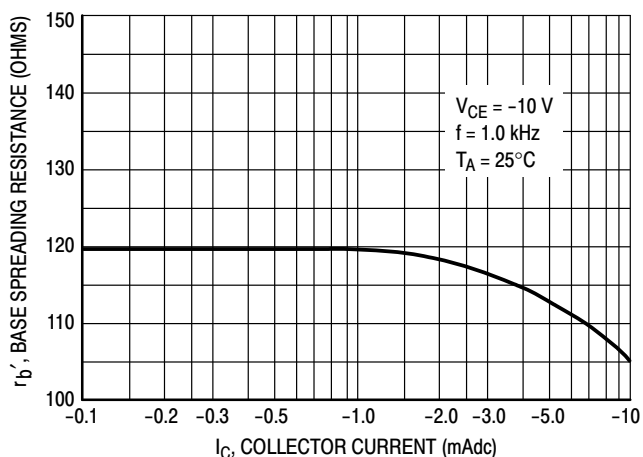
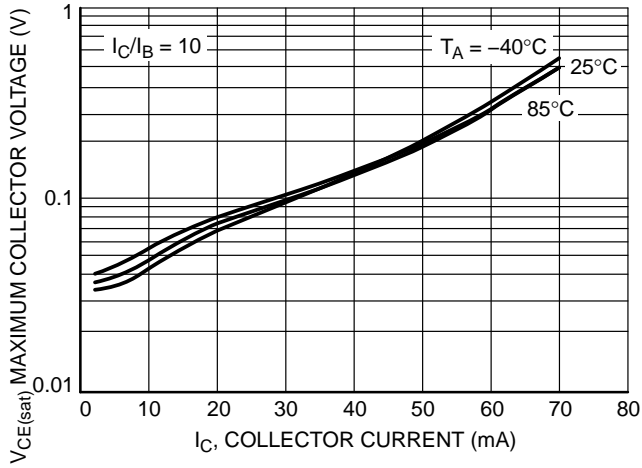


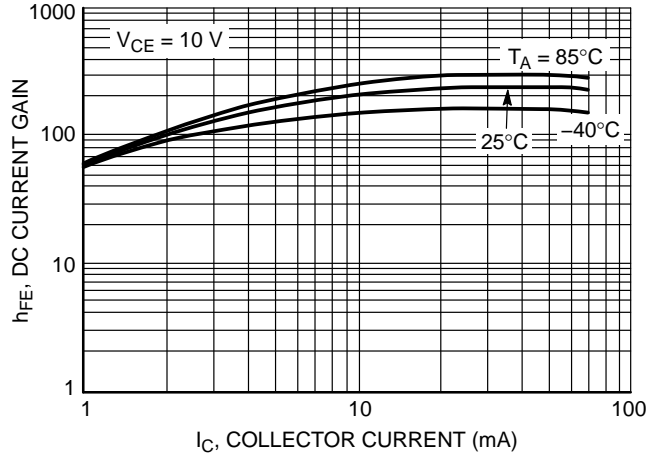
Figure 6. Base Spreading Resistance

# NSTB60BDW1

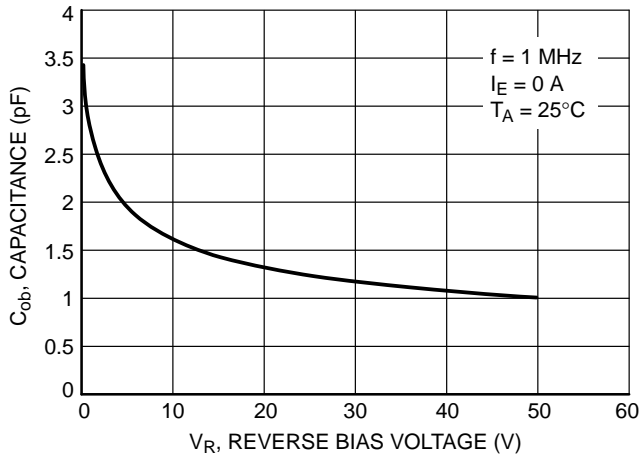
## TYPICAL ELECTRICAL CHARACTERISTICS – NPN Transistor



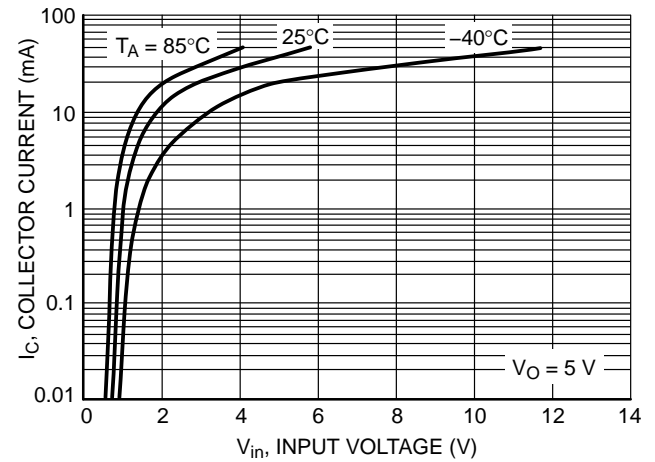
**Figure 7. Maximum Collector Voltage versus Collector Current**



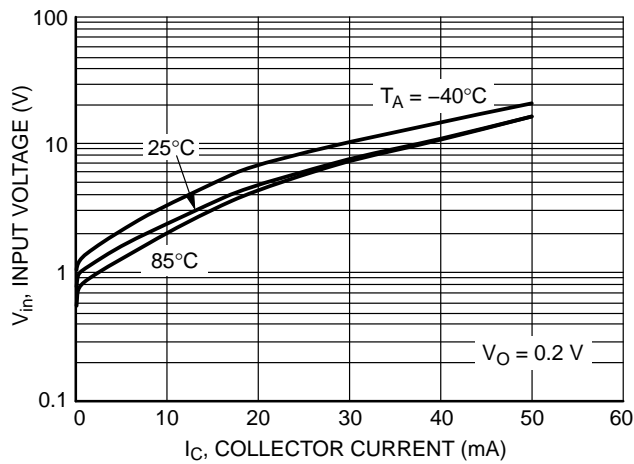
**Figure 8. DC Current Gain**



**Figure 9. Output Capacitance**



**Figure 10. Output Current versus Input Voltage**



**Figure 11. Input Voltage versus Output Current**

# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

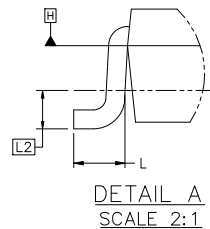
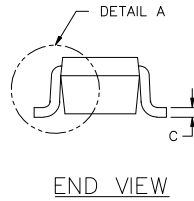
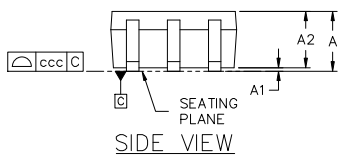
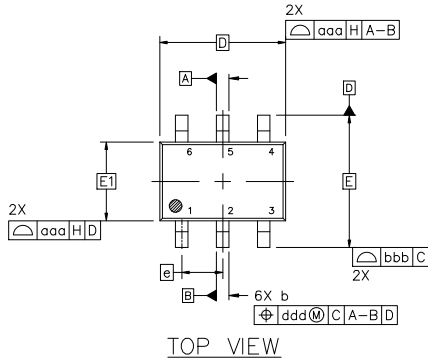


**SC-88 2.00x1.25x0.90, 0.65P**  
CASE 419B-02  
ISSUE Z

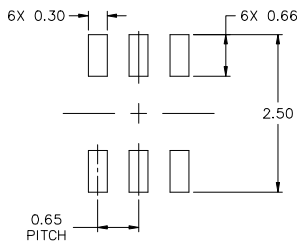
DATE 18 APR 2024

NOTES:

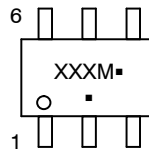
1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
2. ALL DIMENSION ARE IN MILLIMETERS.
3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
4. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.
5. DATUMS A AND B ARE DETERMINED AT DATUM H.
6. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
7. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION b AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.



| DIM | MILLIMETERS |      |      |
|-----|-------------|------|------|
|     | MIN.        | NOM. | MAX. |
| A   | ---         | ---  | 1.10 |
| A1  | 0.00        | ---  | 0.10 |
| A2  | 0.70        | 0.90 | 1.00 |
| b   | 0.15        | 0.20 | 0.25 |
| c   | 0.08        | 0.15 | 0.22 |
| D   | 2.00 BSC    |      |      |
| E   | 2.10 BSC    |      |      |
| E1  | 1.25 BSC    |      |      |
| e   | 0.65 BSC    |      |      |
| L   | 0.26        | 0.36 | 0.46 |
| L2  | 0.15 BSC    |      |      |
| aaa | 0.15        |      |      |
| bbb | 0.30        |      |      |
| ccc | 0.10        |      |      |
| ddd | 0.10        |      |      |



**GENERIC MARKING DIAGRAM\***



- XXX = Specific Device Code
- M = Date Code\*
- = Pb-Free Package

(Note: Microdot may be in either location)  
 \*Date Code orientation and/or position may vary depending upon manufacturing location.  
 \*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ONSEMI SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

**STYLES ON PAGE 2**

|                         |                                    |  |
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**SC-88 2.00x1.25x0.90, 0.65P**  
**CASE 419B-02**  
**ISSUE Z**

DATE 18 APR 2024

|   |   |  |  |  |  |
|---|---|--|--|--|--|
| <b>STYLE 1:</b><br>PIN 1. EMITTER 2<br>2. BASE 2<br>3. COLLECTOR 1<br>4. EMITTER 1<br>5. BASE 1<br>6. COLLECTOR 2 | <b>STYLE 2:</b><br>CANCELLED  | <b>STYLE 3:</b><br>CANCELLED   | <b>STYLE 4:</b><br>PIN 1. CATHODE<br>2. CATHODE<br>3. COLLECTOR<br>4. EMITTER<br>5. BASE<br>6. ANODE               | <b>STYLE 5:</b><br>PIN 1. ANODE<br>2. ANODE<br>3. COLLECTOR<br>4. EMITTER<br>5. BASE<br>6. CATHODE                 | <b>STYLE 6:</b><br>PIN 1. ANODE 2<br>2. N/C<br>3. CATHODE 1<br>4. ANODE 1<br>5. N/C<br>6. CATHODE 2          |
| <b>STYLE 7:</b><br>PIN 1. SOURCE 2<br>2. DRAIN 2<br>3. GATE 1<br>4. SOURCE 1<br>5. DRAIN 1<br>6. GATE 2           | <b>STYLE 8:</b><br>CANCELLED  | <b>STYLE 9:</b><br>PIN 1. EMITTER 2<br>2. EMITTER 1<br>3. COLLECTOR 1<br>4. BASE 1<br>5. BASE 2<br>6. COLLECTOR 2  | <b>STYLE 10:</b><br>PIN 1. SOURCE 2<br>2. SOURCE 1<br>3. GATE 1<br>4. DRAIN 1<br>5. DRAIN 2<br>6. GATE 2           | <b>STYLE 11:</b><br>PIN 1. CATHODE 2<br>2. CATHODE 2<br>3. ANODE 1<br>4. CATHODE 1<br>5. CATHODE 1<br>6. ANODE 2   | <b>STYLE 12:</b><br>PIN 1. ANODE 2<br>2. ANODE 2<br>3. CATHODE 1<br>4. ANODE 1<br>5. ANODE 1<br>6. CATHODE 2 |
| <b>STYLE 13:</b><br>PIN 1. ANODE<br>2. N/C<br>3. COLLECTOR<br>4. EMITTER<br>5. BASE<br>6. CATHODE                 | <b>STYLE 14:</b><br>PIN 1. VREF<br>2. GND<br>3. GND<br>4. IOUT<br>5. VEN<br>6. VCC                            | <b>STYLE 15:</b><br>PIN 1. ANODE 1<br>2. ANODE 2<br>3. ANODE 3<br>4. CATHODE 3<br>5. CATHODE 2<br>6. CATHODE 1     | <b>STYLE 16:</b><br>PIN 1. BASE 1<br>2. EMITTER 2<br>3. COLLECTOR 2<br>4. BASE 2<br>5. EMITTER 1<br>6. COLLECTOR 1 | <b>STYLE 17:</b><br>PIN 1. BASE 1<br>2. EMITTER 1<br>3. COLLECTOR 2<br>4. BASE 2<br>5. EMITTER 2<br>6. COLLECTOR 1 | <b>STYLE 18:</b><br>PIN 1. VIN1<br>2. VCC<br>3. VOUT2<br>4. VIN2<br>5. GND<br>6. VOUT1                       |
| <b>STYLE 19:</b><br>PIN 1. IOUT<br>2. GND<br>3. GND<br>4. V CC<br>5. V EN<br>6. V REF                             | <b>STYLE 20:</b><br>PIN 1. COLLECTOR<br>2. COLLECTOR<br>3. BASE<br>4. EMITTER<br>5. COLLECTOR<br>6. COLLECTOR | <b>STYLE 21:</b><br>PIN 1. ANODE 1<br>2. N/C<br>3. ANODE 2<br>4. CATHODE 2<br>5. N/C<br>6. CATHODE 1               | <b>STYLE 22:</b><br>PIN 1. D1 (i)<br>2. GND<br>3. D2 (i)<br>4. D2 (c)<br>5. VBUS<br>6. D1 (c)                      | <b>STYLE 23:</b><br>PIN 1. Vn<br>2. CH1<br>3. Vp<br>4. N/C<br>5. CH2<br>6. N/C                                     | <b>STYLE 24:</b><br>PIN 1. CATHODE<br>2. ANODE<br>3. CATHODE<br>4. CATHODE<br>5. CATHODE<br>6. CATHODE       |
| <b>STYLE 25:</b><br>PIN 1. BASE 1<br>2. CATHODE<br>3. COLLECTOR 2<br>4. BASE 2<br>5. EMITTER<br>6. COLLECTOR 1    | <b>STYLE 26:</b><br>PIN 1. SOURCE 1<br>2. GATE 1<br>3. DRAIN 2<br>4. SOURCE 2<br>5. GATE 2<br>6. DRAIN 1      | <b>STYLE 27:</b><br>PIN 1. BASE 2<br>2. BASE 1<br>3. COLLECTOR 1<br>4. EMITTER 1<br>5. EMITTER 2<br>6. COLLECTOR 2 | <b>STYLE 28:</b><br>PIN 1. DRAIN<br>2. DRAIN<br>3. GATE<br>4. SOURCE<br>5. DRAIN<br>6. DRAIN                       | <b>STYLE 29:</b><br>PIN 1. ANODE<br>2. ANODE<br>3. COLLECTOR<br>4. EMITTER<br>5. BASE/ANODE<br>6. CATHODE          | <b>STYLE 30:</b><br>PIN 1. SOURCE 1<br>2. DRAIN 2<br>3. DRAIN 2<br>4. SOURCE 2<br>5. GATE 1<br>6. DRAIN 1    |

Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

|                         |                                    |   |
|-------------------------|------------------------------------|---|
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| <b>DESCRIPTION:</b>     | <b>SC-88 2.00x1.25x0.90, 0.65P</b> | <b>PAGE 2 OF 2</b>  |

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